

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A large-diameter SiC wafer, wherein a diameter is increased as a double structure of single crystal SiC and polycrystal SiC by planarly forming a film of polycrystal SiC in a flat plate shape around an outer circumference of a small diameter α -SiC single crystal wafer previously formed as a wafer; and

wherein a top and bottom surface of the small diameter α -SiC single crystal wafer is free of the polycrystal SiC.

2. (Previously Presented) The large-diameter SiC wafer according to claim 1, wherein at least two or more of said small-diameter α -SiC single crystal wafers are placed on a graphite plate.

3. (Currently Amended) ~~The~~ The large-diameter SiC wafer according to claim 1, wherein said polycrystal SiC is a β -SiC manufactured by a CVD method.

4. (Canceled)

5. (Currently Amended) A manufacturing method of a large-diameter SiC wafer comprising the steps of:

~~planarly placing a small diameter α -SiC single crystal wafer previously formed as a wafer on a graphite plate and simultaneously masking a surface of a substrate;~~

~~planarly forming a film of polycrystal SiC around an outer circumference of said wafer from its masking plane side by by depositing polycrystal SiC over the graphite plate and over a surface of the α -SiC single crystal wafer;~~

~~_____ grinding the polycrystal SiC on the surface of the α -SiC single crystal wafer to manufacture an increased-diameter SiC of a double structure in which the polycrystal SiC~~

plate portion is planarly formed around an outer circumference of the small-diameter α -SiC single crystal wafer; and

wherein a top and bottom surface of the small diameter α -SiC single crystal wafer is free of the polycrystal SiC.

6. (New) The manufacture method according to claim 5, further comprising:

masking the α -SiC single crystal wafer with a mask;

depositing the polycrystal SiC over the graphite plate on the mask; and

removing the mask in the grinding, thereby forming the large-diameter SiC wafer.

7. (New) The large-diameter SiC wafer according to claim 1, wherein a diameter of the large-diameter SiC wafer is about three times larger than a diameter of the α -SiC single crystal wafer.